

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	35	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	80	mA
I_H	$I_T=500mA$	-	-	70	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	1000	-	-	V/ μs
t_{on}	$I_G=40mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$	-	2	-	μs
t_{off}		-	60	-	

STATIC CHARACTERISTICS

Symbol	Parameter
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ORDERING INFORMATION

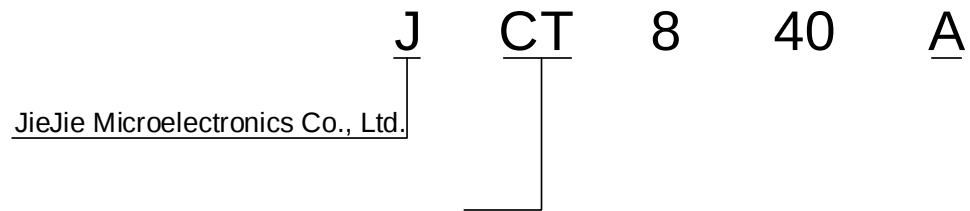


FIG.1: Maximum power dissipation versus RMS on-state current

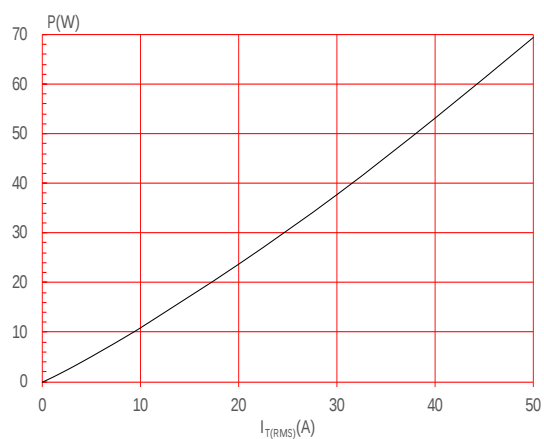
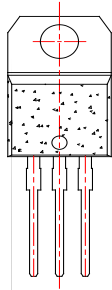
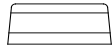


FIG.2: RMS on-state current versus case temperature



PACKAGE MECHANICAL DATA



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